Dual 1-of-4 Decoder/ Demultiplexer

High–Performance Silicon–Gate CMOS

The MC74HC139A is identical in pinout to the LS139. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of two independent 1–of–4 decoders, each of which decodes a two–bit Address to one–of–four active–low outputs. Active–low Selects are provided to facilitate the demultiplexing and cascading functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output, and utilizing the Select as a data input.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 100 FETs or 25 Equivalent Gates



		6		Out	puts	
Select	A1	A0	Y0	Y1	Y2	Y3
н	Х	Х	Н	Н	Н	Н
L	L	L	L	Н	Н	Н
L	L	н	Н	L	Н	Н
L	Н	L	Н	Н	L	Н
L	Н	Н	Н	Н	Н	L



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A = Assembly Location

WL = Wafer Lot

YY = Year WW = Work Week

VVV = Work Week

PIN ASSIGNMENT

-			
SELECT _a	1•	16	□ v _{cc}
ао _а С	2	15	SELECT _b
_{А1а} С	3	14	A0b
yo _a C	4	13	A1b
Ү1 _а [5	12] YO _b
Y2 _a [6	11] Y1 _b
үз _а [7	10] Y2 _b
gnd [8	9] үз _b

ORDERING INFORMATION

Device	Package	Shipping
MC74HC139AN	PDIP-16	2000 / Box
MC74HC139AD	SOIC-16	48 / Rail
MC74HC139ADR2	SOIC-16	2500 / Reel

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
Vin	DC Input Voltage (Referenced to GND)	– 1.5 to V _{CC} + 1.5	V
Vout	DC Output Voltage (Referenced to GND)	– 0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
lout	DC Output Current, per Pin	± 25	mA
ICC	DC Supply Current, V_{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	– 65 to + 150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: – 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Мах	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			VCC	V
TA	Operating Temperature, All Package Types			+ 125	°C
t _r , t _f	Input Rise and Fall Time V (Figure 1) V V	/ _{CC} = 2.0 V / _{CC} = 4.5 V / _{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	VCC V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
VIL	Maximum Low–Level Input Voltage	$\begin{array}{l} V_{out} = 0.1 \ V \ \text{or} \ V_{CC} - 0.1 \ V \\ I_{out} \ \leq \ 20 \ \mu\text{A} \end{array}$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{array}{ll} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 4.0 \text{ mA} \\ I_{out} \leq 5.2 \text{ mA} \end{array}$	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{array}{ll} V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 4.0 \text{ mA} \\ I_{out} \leq 5.2 \text{ mA} \end{array}$	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
lin	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

			Guaranteed Limit		mit	
Symbol	Parameter	V _{CC} V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
^t PLH, ^t PHL	Maximum Propagation Delay, Select to Output Y (Figures 1 and 3)	2.0 4.5 6.0	115 23 20	145 29 25	175 35 30	ns
^t PLH, ^t PHL	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 3)	2.0 4.5 6.0	115 23 20	145 29 25	175 35 30	ns
ttlh, tthl	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance	—	10	10	10	рF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Decoder)*	55	pF

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS



Figure 1.



Figure 2.



*Includes all probe and jig capacitance

Figure 3. Test Circuit

PIN DESCRIPTIONS

ADDRESS INPUTS

A0_a, A1_a, A0_b, A1_b (Pins 2, 3, 14, 13)

Address inputs. These inputs, when the respective 1–of–4 decoder is enabled, determine which of its four active–low outputs is selected.

CONTROL INPUTS Select_a, Select_b (Pins 1, 15)

Active-low select inputs. For a low level on this input, the outputs for that particular decoder follow the Address

inputs. A high level on this input forces all outputs to a high level.

OUTPUTS

Y0_a - Y3_a, Y0_b - Y3_b (Pins 4 - 7, 12, 11, 10, 9)

Active–low outputs. These outputs assume a low level when addressed and the appropriate Select input is active. These outputs remain high when not addressed or the appropriate Select input is inactive.



EXPANDED LOGIC DIAGRAM (1/2 OF DEVICE)

PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE R**



114.300, 1982. CONTROLLING DIMENSION: INCH. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL. DIMENSION B DOES NOT INCLUDE MOLD FLASH. ROUNDED CORNERS OPTIONAL. INCHES MILLIMETERS
 DIM
 MIN
 MAX
 MIN
 MAX

 A
 0.740
 0.770
 18.80
 19.55
B 0.250 0.270 6.35 6.85 C 3.69 0.39 0.145 0.175 4.44 D 0.015 0.021 0.53 F 0.040 0.070 1.02 1.77 G 0.100 BSC 2.54 BSC Н 0.050 BSC 1.27 BSC
 J
 0.008
 0.0.5

 K
 0.110
 0.130

 0.305
 0.305
 0.305
0.21 0.38 2.80 3.30 M 0.295 0.305 7.50 7.74 0° 10° 0° 10° S 0.020 0.040 0.51 1.01

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



NOTES:

NOTES

1.

2.

3.

4. 5.

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14 5M 1982
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. MAXIMUM MOLD PROTRUSION 0.15 (0.006) DED SIDE 2. 3.

4. PER SIDE.

PER SIDE. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR 5. PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
A	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.2	7 BSC	0.050) BSC	
J	0.19	0.25	0.008	0.009	
К	0.10	0.25	0.004	0.009	
М	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

Notes

Notes

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